

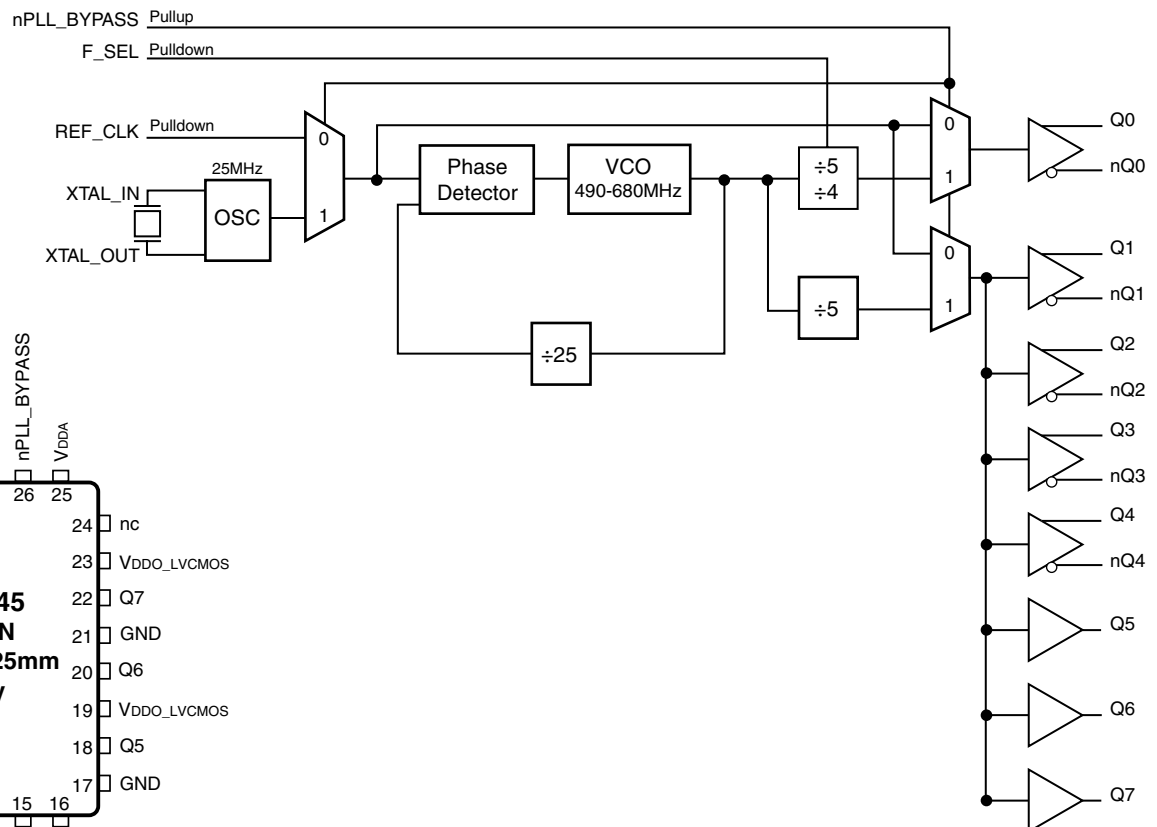
General Description

The ICS8440258I-45 is a eight output synthesizer optimized to generate Gigabit and 10 Gigabit Ethernet clocks. Using a 25MHz, 18pF parallel resonant crystal, the device will generate both 156.25MHz and 125MHz clocks with mixed LVDS and LVCMOS/LVTTL output levels. The ICS8440258I-45 uses IDT's 3RD generation low phase noise VCO technology and can achieve <1ps typical rms phase jitter, easily meeting Ethernet jitter requirements. The ICS8440258I-45 is packaged in a small, 5mm x 5mm VFQFN package that is optimum for applications with space limitations.

Features

- One differential LVDS output at 156.25MHz or 125MHz
Four differential LVDS outputs at 125MHz
Three LVC MOS/LVTTL single-ended outputs at 125MHz
- Selectable crystal oscillator interface or LVC MOS/LVTTL single-ended input and PLL bypass from a single select pin
- VCO range: 490MHz - 680MHz
- RMS phase jitter @ 125MHz, using a 25MHz crystal (1.875MHz - 20MHz): 0.41ps (typical), LVDS outputs
- RMS phase jitter @ 156.25MHz, using a 25MHz crystal (1.875MHz - 20MHz): 0.43ps (typical), Q0, nQ0 output
- Full 2.5V supply mode
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Block Diagram



Pin Assignment

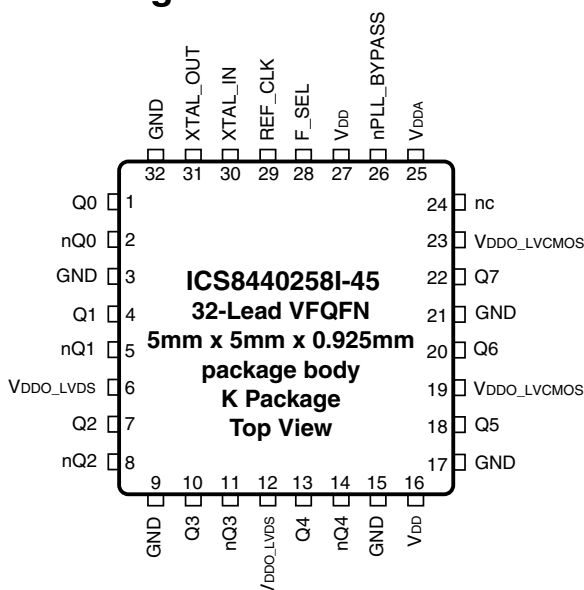


Table 1. Pin Descriptions

Number	Name	Type		Description
1, 2	Q0, nQ0	Output		Differential clock outputs. LVDS interface levels.
3, 9, 15, 17, 21, 32	GND	Power		Power supply ground.
4, 5	Q1, nQ1	Output		Differential clock outputs. LVDS interface levels.
6, 12	V _{DDO_LVDS}	Power		Output supply pins for Q[0:4], nQ[0:4] LVDS outputs.
7, 8	Q2, nQ2	Output		Differential clock outputs. LVDS interface levels.
10, 11	Q3, nQ3	Output		Differential clock outputs. LVDS interface levels.
13, 14	Q4, nQ4	Output		Differential clock outputs. LVDS interface levels.
16, 27	V _{DD}	Power		Core supply pins.
18, 20, 22	Q5, Q6, Q7	Output		Single-ended clock outputs. LVCMOS/LVTTL interface levels.
19, 23	V _{DDO_LVCMOS}	Power		Output supply pins for Q[5:7] LVCMOS outputs.
24	nc	Unused		No connect.
25	V _{DDA}	Power		Analog supply pin.
26	nPLL_BYPASS	Input	Pullup	Input select and PLL bypass control pin. See Table 3B. LVCMOS/LVTTL interface levels.
28	F_SEL	Input	Pulldown	Frequency select pin. See Table 3A. LVCMOS/LVTTL interface levels.
29	REF_CLK	Input	Pulldown	Single-ended reference clock input. LVCMOS/LVTTL interface levels.
30, 31	XTAL_IN, XTAL_OUT	Input		Crystal oscillator interface. XTAL_OUT is the output, XTAL_IN is the input.

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance				4		pF
C _{PD}	Power Dissipation Capacitance (per output)	Q[5:7]	V _{DDO_LVCMOS} = 2.625V		15		pF
R _{PULLUP}	Input Pullup Resistor				51		kΩ
R _{PULLDOWN}	Input Pulldown Resistor				51		kΩ
R _{OUT}	Output Impedance	Q[5:7]	V _{DDO_LVCMOS} = 2.625V		25		Ω

Function Tables

Table 3A. F_SEL Frequency Select Function Table

Input		Output Frequency
F_SEL	Output Divider Value	Q0, nQ0 (MHz)
0	÷5	125 (default)
1	÷4	156.25

Table 3B. PLL Bypass and Input Select Function Table

Inputs		
nPLL_BYPASS	PLL BYPASS	Input Selected
0	PLL Bypassed	REF_CLK
1	PLL Enabled	XTAL_IN, XTAL_OUT (default)

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V_{DD}	4.6V
Inputs, V_I XTAL_IN Other Inputs	0V to V_{DD} -0.5V to $V_{DD} + 0.5V$
Outputs, I_O (LVCMOS)	-0.5V to $V_{DDO_LVCMOS} + 0.5V$
Outputs, I_O (LVDS) Continuous Current Surge Current	10mA 15mA
Operating Temperature Range, T_A	-40°C to +85°C
Package Thermal Impedance, θ_{JA}	33.1°C/W (0 mps)
Storage Temperature, T_{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, $V_{DD} = V_{DDO_LVCMOS} = V_{DDO_LVDS} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Core Supply Voltage		2.375	2.5	2.625	V
V_{DDA}	Analog Supply Voltage		$V_{DD} - 0.32$	2.5	V_{DD}	V
V_{DDO_LVCMOS} , V_{DDO_LVDS}	Output Supply Voltage		2.375	2.5	2.625	V
I_{DD}	Power Supply Current				125	mA
I_{DDA}	Analog Supply Current				32	mA
I_{DDO_LVCMOS}	LVCMOS Output Supply Current				5	mA
I_{DDO_LVDS}	LVDS Output Supply Current				150	mA

Table 4B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = V_{DDO_LVCMOS} = 2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage			1.7		$V_{DD} + 0.3$	V
V_{IL}	Input Low Voltage			-0.3		0.7	V
I_{IH}	Input High Current	REF_CLK, F_SEL	$V_{DD} = V_{IN} = 2.625V$			150	μA
		nPLL_BYPASS	$V_{DD} = V_{IN} = 2.625V$			5	μA
I_{IL}	Input Low Current	REF_CLK, F_SEL	$V_{DD} = 2.625V, V_{IN} = 0V$	-5			μA
		nPLL_BYPASS	$V_{DD} = 2.625V, V_{IN} = 0V$	-150			μA
V_{OH}	Output High Voltage	Q[5:7]	$I_{OH} = -12mA$	2.6			V
V_{OL}	Output Low Voltage	Q[5:7]	$I_{OL} = 12mA$			0.5	V

Table 4C. LVDS DC Characteristics, $V_{DD} = V_{DDO_LVDS} = 2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OD}	Differential Output Voltage		300	400	545	mV
ΔV_{OD}	V_{OD} Magnitude Change				50	mV
V_{OS}	Offset Voltage		1.25	1.35	1.5	V
ΔV_{OS}	V_{OS} Magnitude Change				50	mV

Table 5. Crystal Characteristics

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation			Fundamental		
Frequency			25		MHz
Equivalent Series Resistance				50	Ω
Shunt Capacitance				7	pF
Drive Level				1	mW

NOTE: Characterized using an 18pF parallel resonant crystal.

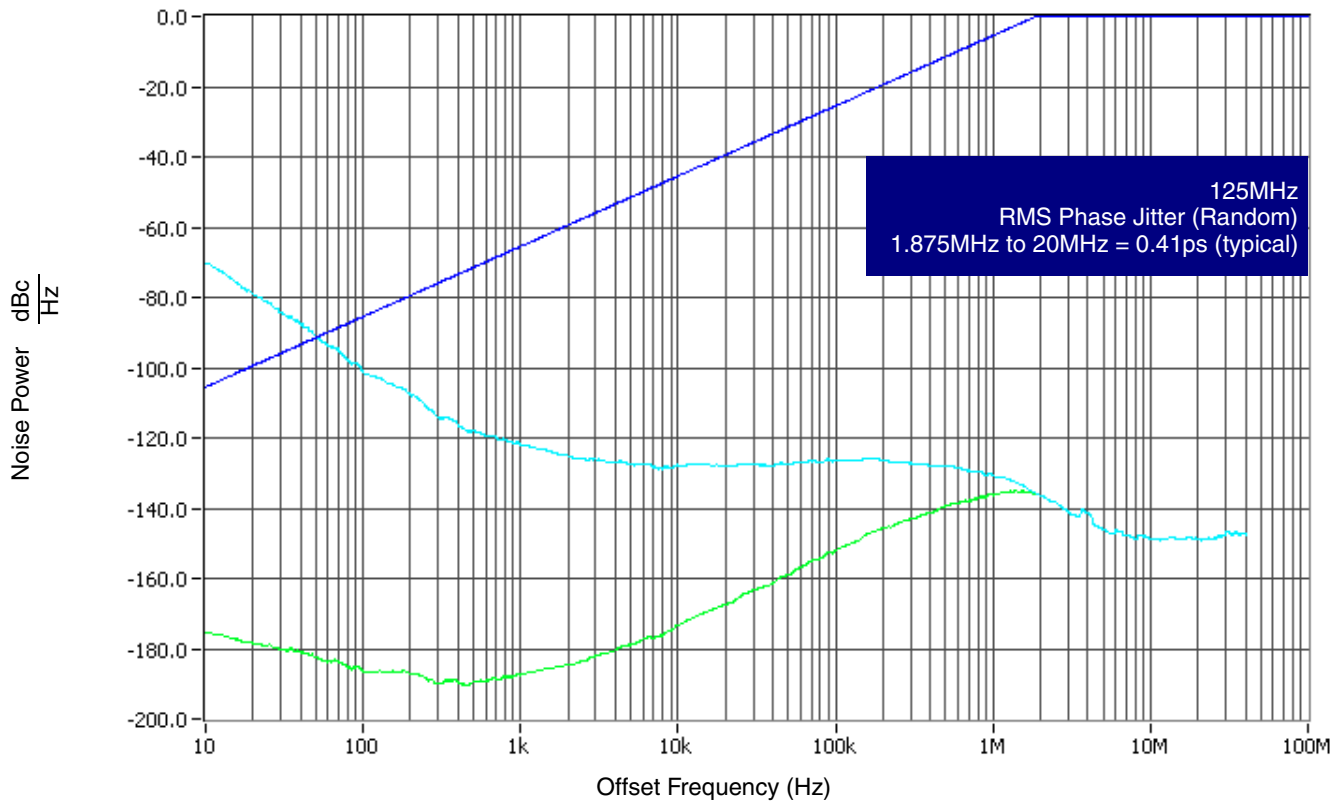
AC Electrical Characteristics

Table 6. AC Characteristics, $V_{DD} = V_{DDO_LVCMOS} = V_{DDO_LVDS} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

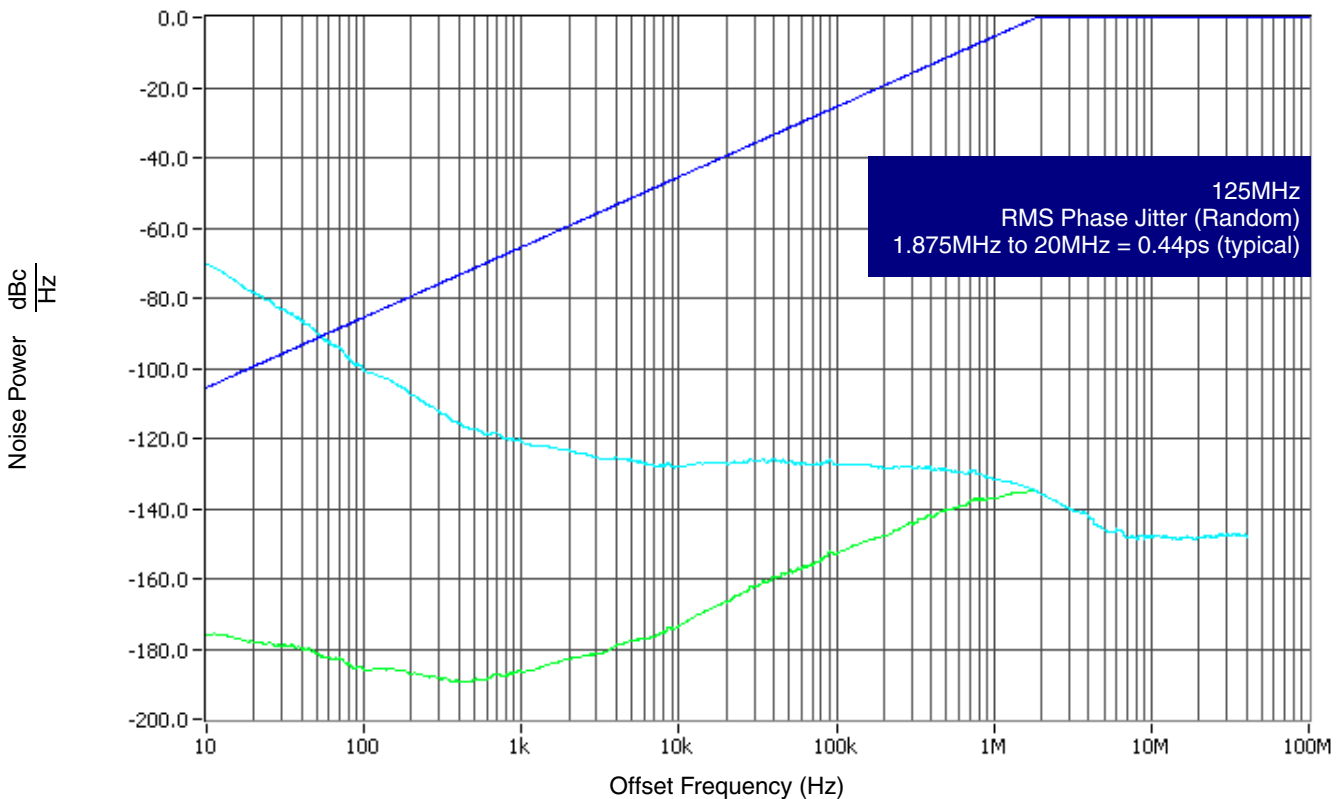
Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f_{out}	Output Frequency	Q[0:4], nQ[0:4]			125		MHz
		Q[5:7]			125		MHz
		Q0, nQ0			156.25		MHz
$\text{f}_{jit}(\emptyset)$	RMS Phase Noise Jitter	Q[0:4], nQ[0:4]	125MHz, Integration Range: 1.875MHz - 20MHz		0.41		ps
		Q0, nQ0	156.25MHz, Integration Range: 1.875MHz - 20MHz		0.43		ps
		Q[5:7]	125MHz, Integration Range: 1.875MHz - 20MHz		0.44		ps
t_R / t_F	Output Rise/Fall Time	Q[0:4], nQ[0:4]	125MHz, 20% to 80%	200		650	ps
		Q0, nQ0	156.25MHz, 20% to 80%	175		615	ps
		Q[5:7]	125MHz, 20% to 80%	600		1800	ps
odc	Output Duty Cycle PLL Mode	Q[0:4], nQ[0:4]	125MHz	46		54	%
		Q0, nQ0	156.25MHz	48		52	%
		Q[5:7]	125MHz	44		56	%
odc	Output Duty Cycle, Bypass Mode	Q[0:4], nQ[0:4]	125MHz	47		53	%
		Q0, nQ0	156.25MHz	47		53	%
		Q[5:7]	125MHz	47		53	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

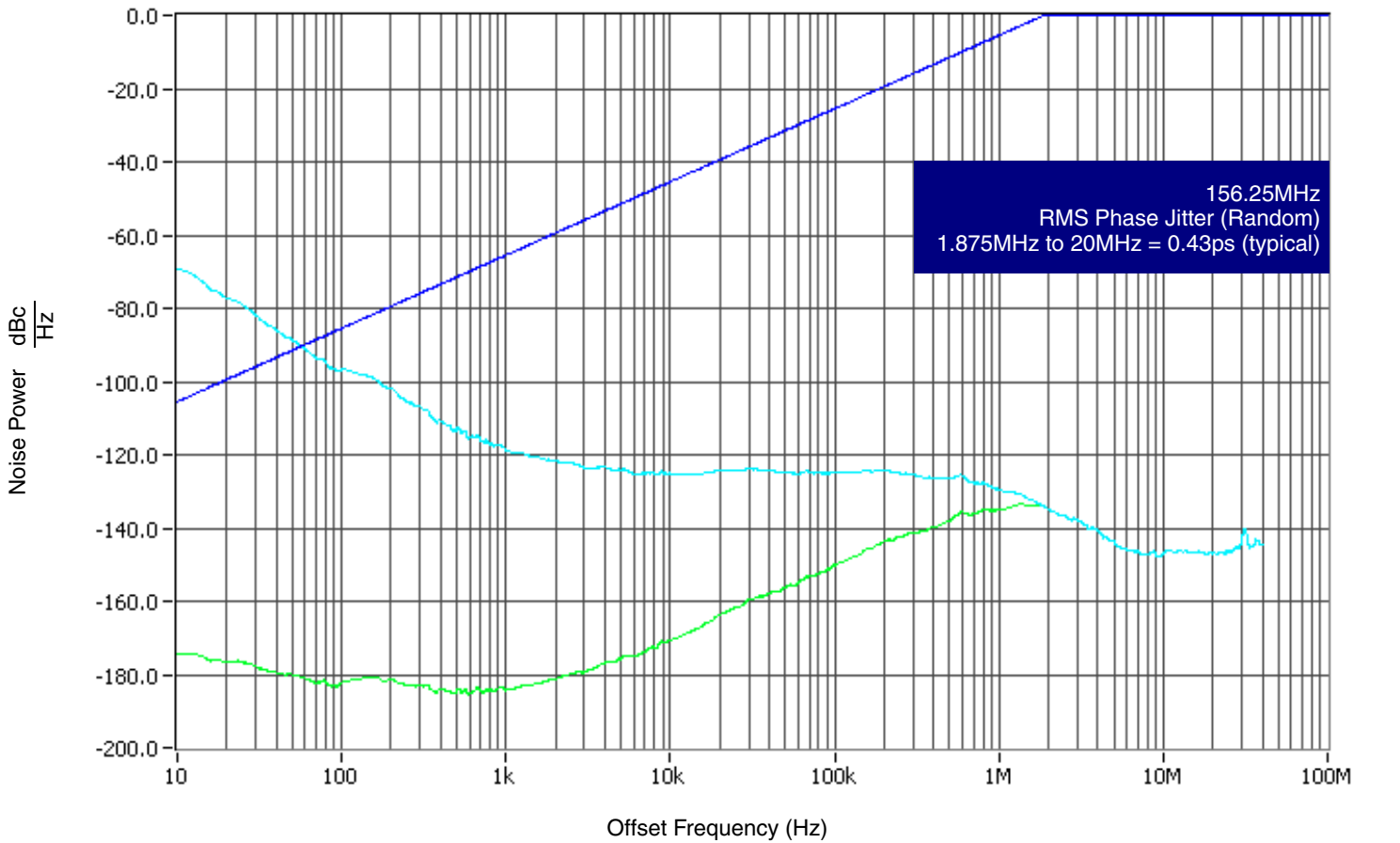
Typical Phase Noise at 125MHz (Q[0:4], nQ[0:4])



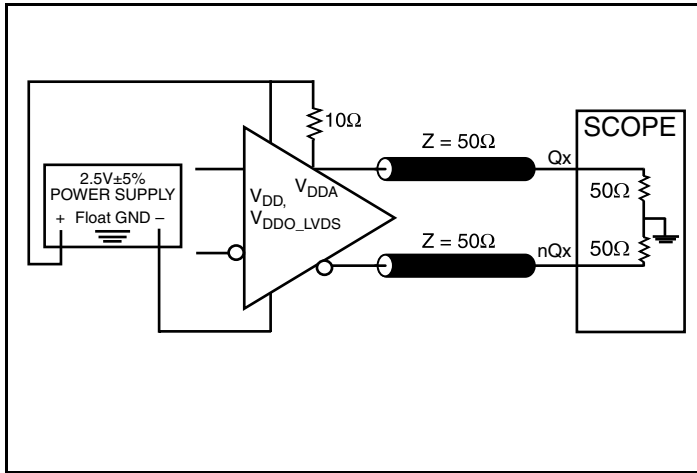
Typical Phase Noise at 125MHz (Q[5:7])



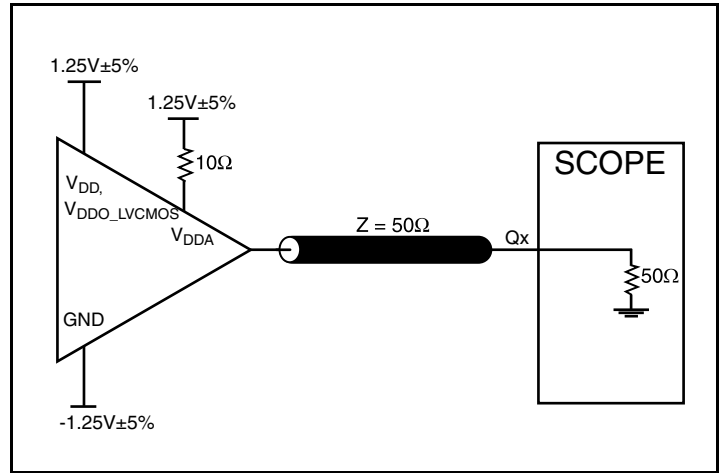
Typical Phase Noise at 156.25MHz (Q0, nQ0)



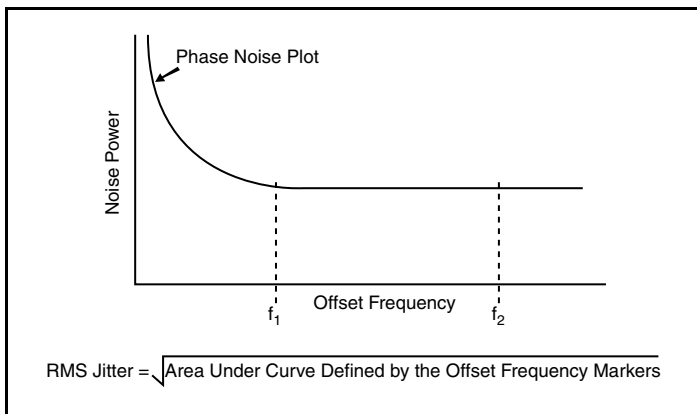
Parameter Measurement Information



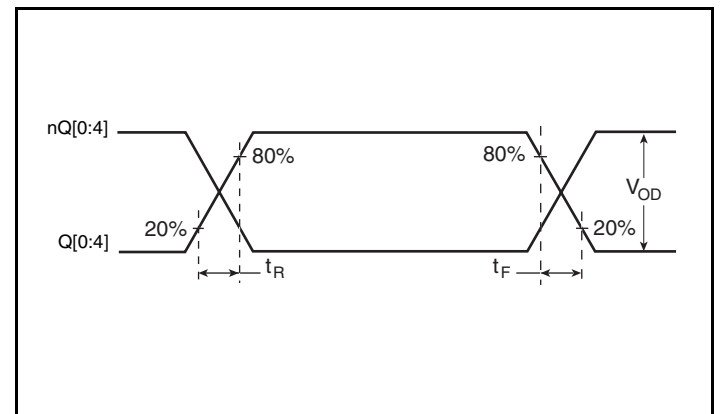
LVDS Output Load AC Test Circuit



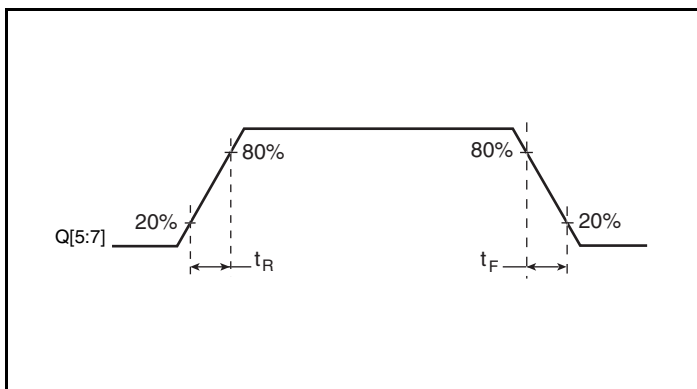
LVCMOS Output Load AC Test Circuit



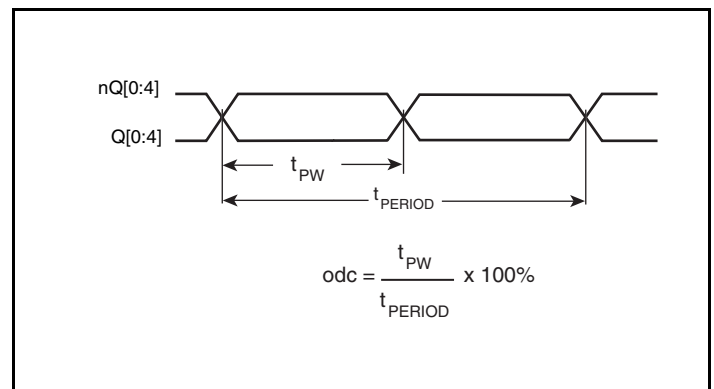
RMS Phase Jitter



LVDS Output Rise/Fall Time

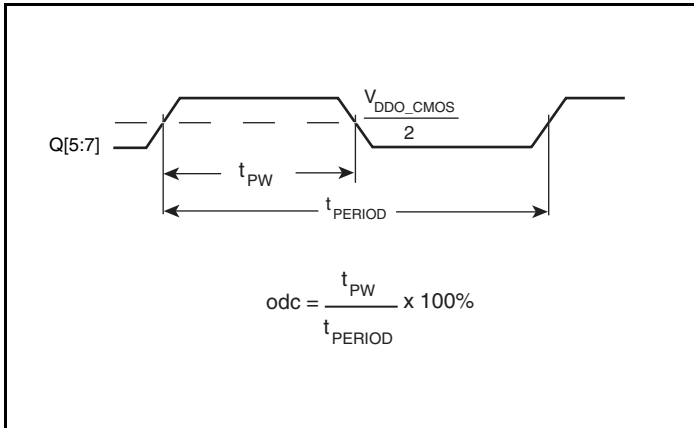


LVCMOS Output Rise/Fall Time

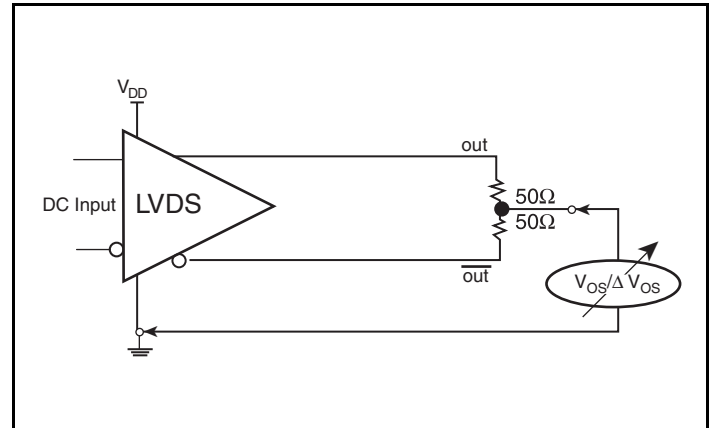


Differential Output Duty Cycle/Pulse Width/Period

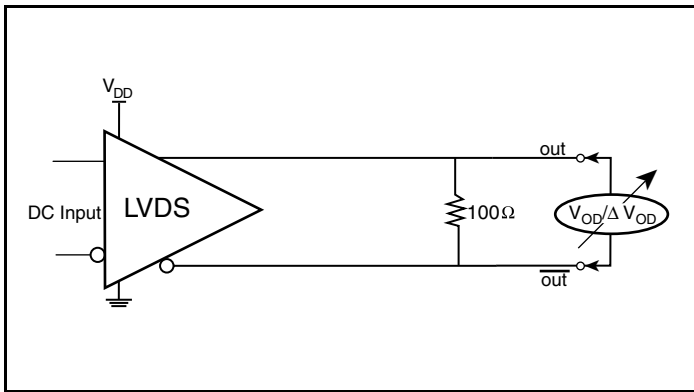
Parameter Measurement Information, continued



Single-Ended Output Duty Cycle/Pulse Width/Period



Offset Voltage Setup



Differential Output Voltage Setup

Applications Information

Overdriving the XTAL Interface

The XTAL_IN input can be overdriven by an LVCMOS driver or by one side of a differential driver through an AC coupling capacitor. The XTAL_OUT pin can be left floating. The amplitude of the input signal should be between 500mV and 1.8V and the slew rate should not be less than 0.2V/nS. For 3.3V LVCMOS inputs, the amplitude must be reduced from full swing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. *Figure 1A* shows an example of the interface diagram for a high speed 3.3V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver (R_o) and the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This

can be done in one of two ways. First, R_1 and R_2 in parallel should equal the transmission line impedance. For most 50Ω applications, R_1 and R_2 can be 100Ω. This can also be accomplished by removing R_1 and changing R_2 to 50Ω. The values of the resistors can be increased to reduce the loading for a slower and weaker LVCMOS driver. *Figure 1B* shows an example of the interface diagram for an LVPECL driver. This is a standard LVPECL termination with one side of the driver feeding the XTAL_IN input. It is recommended that all components in the schematics be placed in the layout. Though some components might not be used, they can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a quartz crystal as the input.

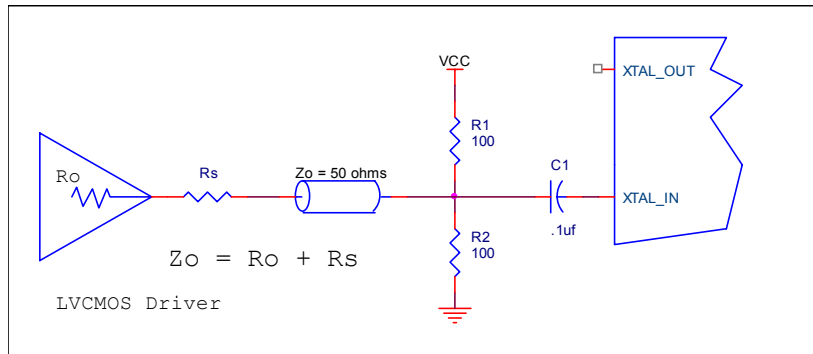


Figure 1A. General Diagram for LVCMOS Driver to XTAL Input Interface

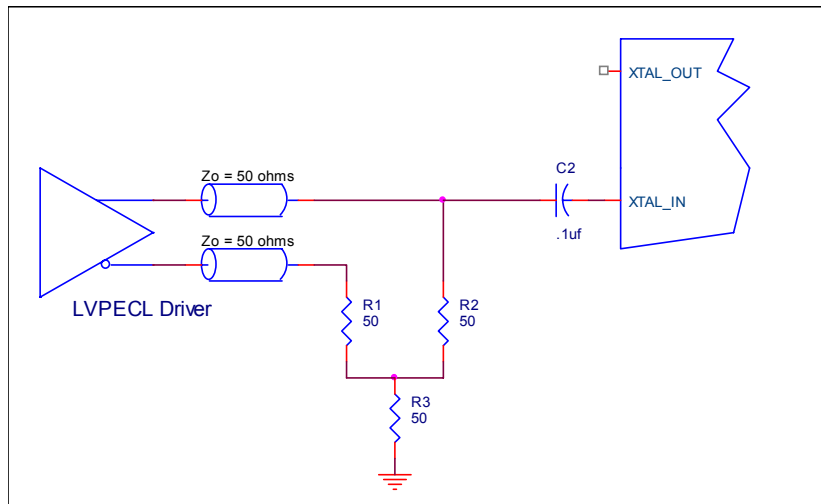


Figure 1B. General Diagram for LVPECL Driver to XTAL Input Interface

LVDS Driver Termination

A general LVDS interface is shown in *Figure 2*. Standard termination for LVDS type output structure requires both a 100Ω parallel resistor at the receiver and a 100Ω differential transmission line environment. In order to avoid any transmission line reflection issues, the 100Ω resistor must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The standard

termination schematic as shown in Figure 2 can be used with either type of output structure. If using a non-standard termination, it is recommended to contact IDT and confirm if the output is a current source or a voltage source type structure. In addition, since these outputs are LVDS compatible, the amplitude and common mode input range of the input receivers should be verified for compatibility with the output.

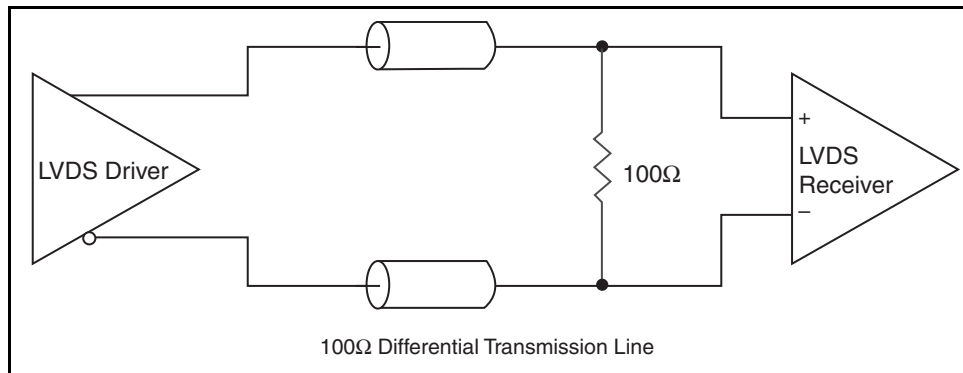


Figure 2. Typical LVDS Driver Termination

Recommendations for Unused Input and Output Pins

Inputs:

LVCMOS Control Pins

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A $1k\Omega$ resistor can be used.

Crystal Inputs

For applications not requiring the use of the crystal oscillator input, both XTAL_IN and XTAL_OUT can be left floating. Though not required, but for additional protection, a $1k\Omega$ resistor can be tied from XTAL_IN to ground.

REF_CLK Input

For applications not requiring the use of the reference clock, it can be left floating. Though not required, but for additional protection, a $1k\Omega$ resistor can be tied from the REF_CLK to ground.

Outputs:

LVDS Outputs

All unused LVDS outputs should be terminated with 100Ω resistor between the differential pair.

LVCMOS Outputs

All unused LVCMOS output can be left floating. There should be no trace attached.

VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 3*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor's Thermally Electrically Enhance Leadframe Base Package, Amkor Technology.

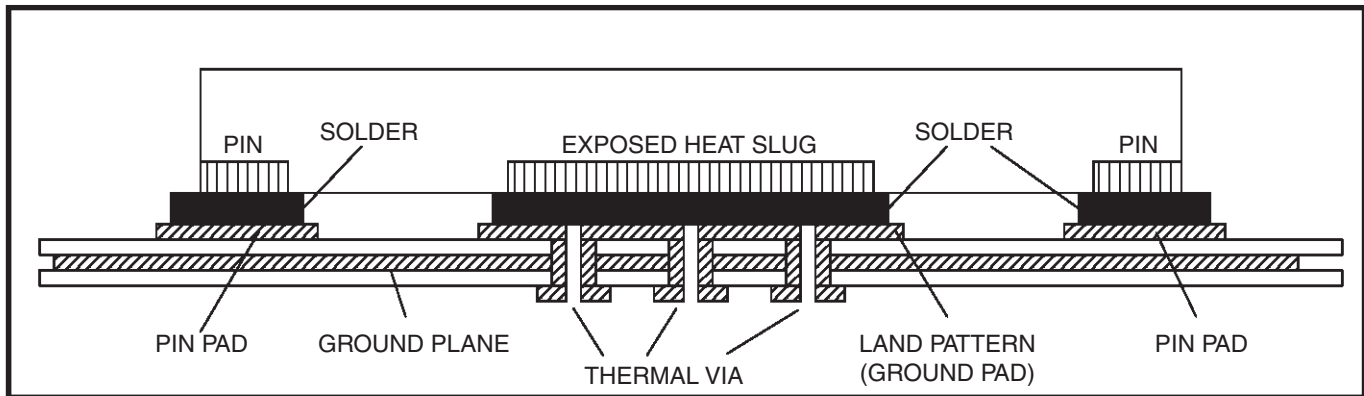


Figure 3. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)

Power Considerations

This section provides information on power dissipation and junction temperature for the ICS8440258I-45. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS8440258I-45 is the sum of the core power plus the power dissipation in the load(s). The following is the power dissipation for $V_{DD} = 2.5V + 5\% = 2.625V$, which gives worst case results.

Core and LVDS, LVCMOS Output Power Dissipation

- Power (core) = $V_{DD_MAX} * (I_{DD} + I_{DDO_LVDS} + I_{DDO_LVCMOS} + I_{DDA}) = 2.625V * (125mA + 150mA + 5mA + 32mA) = 819mW$

LVCMOS Output Power Dissipation

- Output Impedance R_{OUT} Power Dissipation due to Loading 50Ω to $V_{DDO}/2$
Output Current $I_{OUT} = V_{DDOX_MAX} / [2 * (50\Omega + R_{OUT})] = 2.625V / [2 * (50\Omega + 25\Omega)] = 17.5mA$
- Power Dissipation on the R_{OUT} per LVCMOS output
Power (R_{OUT}) = $R_{OUT} * (I_{OUT})^2 = 25\Omega * (17.5mA)^2 = 7.7mW$ per output
- Total Power Dissipation on the R_{OUT}
Total Power (R_{OUT}) = $7.7mW * 3 = 23mW$
- Dynamic Power Dissipation at 125MHz, (Q[5:7])
Power (125MHz) = $C_{PD} * Frequency * (V_{DDO})^2 = 15pF * 125MHz * (2.625V)^2 = 12.92mW$ per output
Total Power (125MHz) = $12.92mW * 3 = 38.8mW$

Total Power Dissipation

- Total Power**
= Power (core, LVDS) + Total Power(R_{OUT}) + Total Power (125MHz)
= $819mW + 23mW + 38.8mW$
= **880.73mW**

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad, and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_{total} + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_{total} = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 33.1°C/W per Table 7 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^{\circ}\text{C} + 0.881\text{W} * 33.1^{\circ}\text{C/W} = 114.2^{\circ}\text{C. This is below the limit of } 125^{\circ}\text{C.}$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 7. Thermal Resistance θ_{JA} for 32 Lead VFQFN, Forced Convection

Meters per Second	0	1	3
Multi-Layer PCB, JEDEC Standard Test Boards	33.1°C/W	28.1°C/W	25.4°C/W

Reliability Information

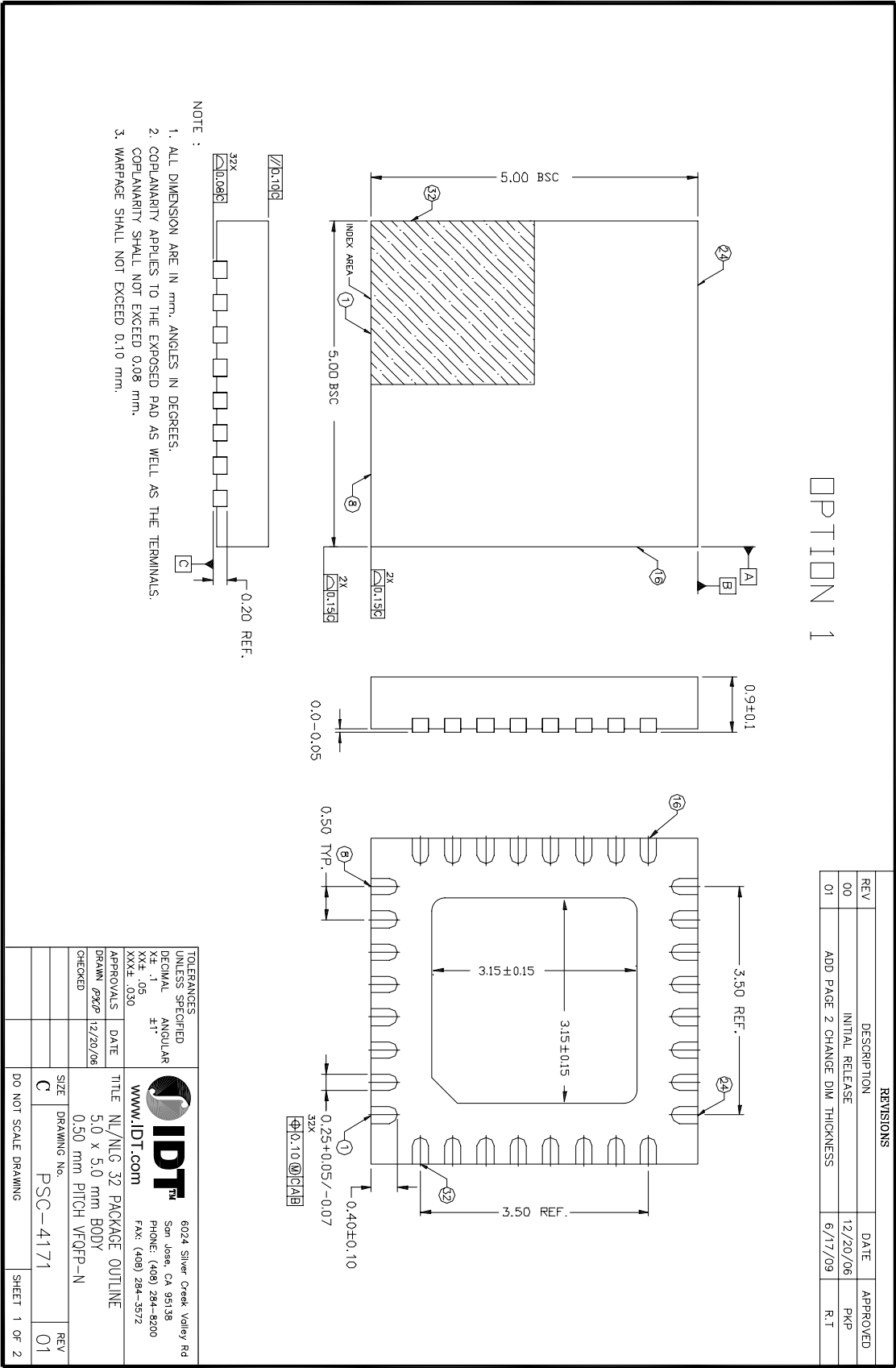
Table 8. θ_{JA} vs. Air Flow Table for a 32 Lead VFQFN

θ_{JA} vs. Air Flow			
Meters per Second	0	1	3
Multi-Layer PCB, JEDEC Standard Test Boards	33.1°C/W	28.1°C/W	25.4°C/W

Transistor Count

The transistor count for ICS8440258I-45 is: 2975

32 Lead VFQFN Package Outline and Package Dimensions



Ordering Information

Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
8440258AKI-45LF	258AI45L	"Lead-Free" 32 Lead VFQFN	Tray	-40°C to 85°C
8440258AKI-45LFT	258AI45L	"Lead-Free" 32 Lead VFQFN	2500 Tape & Reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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